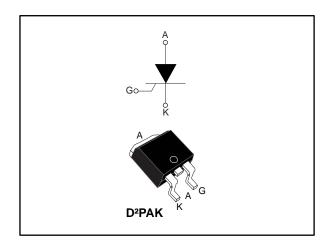


TN1605H-6G

High temperature 16 A SCRs

Datasheet - production data



Description

Designed with high immunity switching to external surges, this device offers robust switching up to its 150°C maximum T_j.

The combination of noise immunity and low gate triggering current allows to design strong and compact control circuit.

Table 1: Device summary

Order code	Package	V _{DRM} /V _{RRM}	lgт	
TN1605H-6G	D²PAK	600	6 mA	

Features

- High junction temperature: T_i = 150 °C
- Gate triggering current I_{GT} = 6 mA
- High noise immunity dV/dt = 200 V/μs up to 150 °C
- Blocking voltage V_{DRM}/V_{RRM} = 600 V
- High turn-on current rise dI/dt: 100 A/µs
- ECOPACK®2 compliant component

Applications

- Motorbikes voltage regulator circuits
- Inrush current limiting circuits
- Motor control circuits and starters
- Light dimmers
- Solid state relays

Characteristics TN1605H-6G

1 Characteristics

Table 2: Absolute maximum ratings (limiting values, $T_j = 25$ °C unless otherwise specified)

Symbol	Para	Value	Unit			
I _{T(RMS)}	RMS on-state current (180 ° conduction angle)		T _c = 133 °C	16	А	
			T _c = 133 °C	10		
IT _(AV)	Average on-state current (180° conduction angle)	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	T _c = 138 °C	8	Α	
	(100 conduction angle)		T _c = 142 °C	6		
l	Non repetitive surge peak	$t_p = 8.3 \text{ ms}$	Trinitial 25 °C	153	Α	
I _{TSM}	on-state current	$t_p = 10 \text{ ms}$	T_j initial = 25 °C	140		
l ² t	I ² t value for fusing	$t_p = 10 \text{ ms}$		98	A ² s	
dl/dt	Critical rate of rise of on-state $I_G = 2 \times I_{GT}$, current $tr \le 100 \text{ ns}$,		f = 60 Hz	100	A/µs	
V _{DRM} /V _{RRM}	Repetitive peak off-state voltage		T _j = 150 °C	600	V	
V _{DSM} /V _{RSM}	Non repetitive surge peak off- state voltage $t_p = 10 \text{ ms}$			700	٧	
P _G (AV)	Average gate power dissipation	1	W			
V _{RGM}	Maximum peak reverse gate voltage			5	V	
I _{GM}	Peak gate current $t_p = 20 \mu s$		T _j = 150 °C	4	Α	
T _{stg}	Storage junction temperature range			-40 to +150	°C	
Tj	Operating junction temperature range			-40 to +150	°C	

Table 3: Dynamic characteristics

Symbol	Parameter	Tj		Value	Unit
		25 °C	Min.	3.5	
lgт	V- 42 V D. = 22 O	Тур.		4.5	mA
	$V_D = 12 \text{ V}, \text{ R}_L = 33 \Omega$	Max.		6	
V _{GT}		Max.		1.3	V
V_{GD}	$V_D = 600, R_L = 3.3 \text{ k}\Omega$	150 °C	Min.	0.15	V
lι	I _G = 1.2 x I _{GT}	25 °C	Max.	40	A
Ін	I _T = 500 mA, gate open	25 C	Max.	20	mA
dV/dt	V _D = 402 V, gate open	150 °C	Min.	200	V/µs
t _{gt}	$I_{TM} = 32 \text{ A}, V_D = 402 \text{ V}, I_G = 12 \text{ mA}, (dI_G/dt)$ $max = 0.2 \text{ A/}\mu\text{s}$	25 °C	Тур.	1.9	μs
tq	$I_{TM} = 32 \text{ A}, V_D = 402 \text{ V}, (dl/dt)_{off} = 30 \text{ A/}\mu\text{s}, V_R = 25 \text{ V}, dV_D/dt = 20 \text{ V/}\mu\text{s}$	150 °C	Тур.	70	μs

TN1605H-6G Characteristics

Table 4: Static electrical characteristics

Symbol	Test conditions	Tj		Value	Unit
V _{TM}	$I_{TM} = 32 \text{ A}, t_p = 380 \ \mu s$	25 °C	Max.	1.6	V
V _{TO}	Threshold on-state voltage	150 °C	Max.	0.82	V
R _D	Dynamic resistance	150 °C	Max.	25	mΩ
		25 °C		5	μΑ
I _{DRM} /I _{RRM} V _{DRM} = V _{RRM}	V _{DRM} = V _{RRM}	125 °C	Max.	1.5	A
		150 °C		3.1	mA

Table 5: Thermal resistance

Symbol	Paramete	Value	Unit		
R _{th(j-c)}	Junction to case (DC)		Max.	1.1	°C/W
R _{th(j-a)}	Junction to ambient (DC) $S^{(1)} = 1 \text{ cm}2$		Тур.	45	C/VV

Notes:

⁽¹⁾S = copper surface under tab

TN1605H-6G **Characteristics**

 $I_{T(AV)}(A)$

10

15

150

Characteristics (curves) 1.1

8

6

0

0.0

25

Figure 1: Maximum average power dissipation versus average on-state current 18 16 $\alpha = 180$ DC α = 120 ° 14 α = 90 12 α = 30 $^{\circ}$ 10

Figure 2: Average and DC on-state current versus case temperature $I_{\mathsf{T}(\mathsf{AV})}(\mathsf{A})$ DC 18 16 14 12 $\alpha = 180^{\circ}$ 10 α = 120 8 6 $\alpha = 60$ α = 30 ° 4 2 T_C(°C) 0 0 100 125 150

Figure 3: Average and DC on-state current versus ambient temperature $\mathsf{I}_{\mathsf{T}(\mathsf{AV})}(\mathsf{A})$ 3.0 1.0 0.5

T_a(°C)

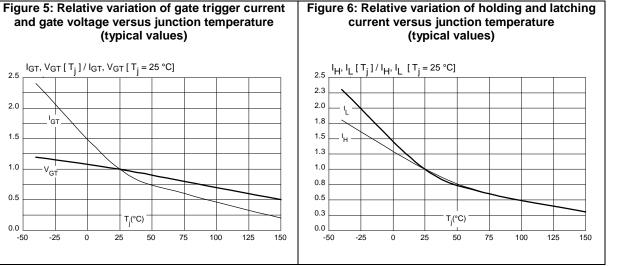
50

75

100

Figure 4: Relative variation of thermal impedance versus pulse duration $K = [Z_{th}/R_{th}]$ 1.0E+00 1.0E-01

and gate voltage versus junction temperature (typical values) I_{GT} , V_{GT} [T_i] / I_{GT} , V_{GT} [T_i = 25 °C] 1.0 0.5 T_i(°C) 0.0



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TN1605H-6G Characteristics

Figure 7: Relative variation of static dV/dt immunity versus junction temperature (typical values)

dV/dt [Tj] / dV/dt [Tj= 150 °C]

Above test equipment capability

Above test equipment capability

T_j (°C)

100

125

75

0 L 25

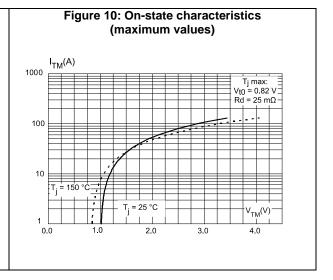
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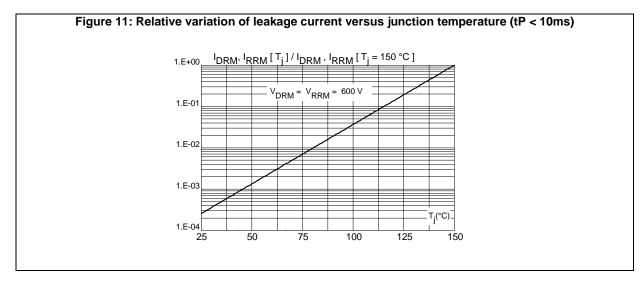
Figure 8: Surge peak on-state current versus number of cycles

150
Non repetitive T_j = 25 °C
One cycle
Number of cycles

1 10 100 1000

Figure 9: Non repetitive surge peak on-state current versus sinusoidal pulse width ($t_P < 10 \text{ ms}$). $t_{TSM}(A)$ $t_$







Package information TN1605H-6G

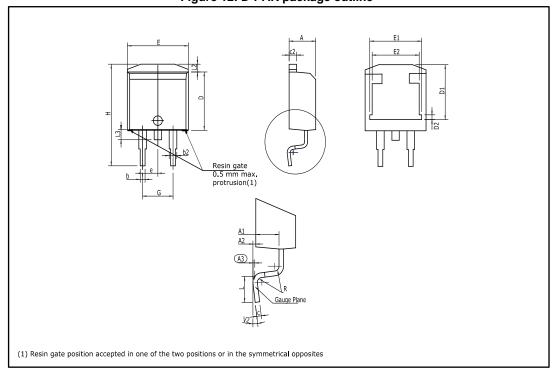
2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Epoxy meets UL 94,V0
- Lead-free package

2.1 D²PAK package information

Figure 12: D²PAK package outline



TN1605H-6G Package information

Table 6: D²PAK package mechanical data

	Dimensions					
Ref.		Millimeters				
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	4.30		4.60	0.1693		0.1811
A1	2.49		2.69	0.0980		0.1059
A2	0.03		0.23	0.0012		0.0091
A3		0.25			0.0098	
b	0.70		0.93	0.0276		0.0366
b2	1.25		1.7	0.0492		0.0669
С	0.45		0.60	0.0177		0.0236
c2	1.21		1.36	0.0476		0.0535
D	8.95		9.35	0.3524		0.3681
D1	7.50		8.00	0.2953		0.3150
D2	1.30		1.70	0.0512		0.0669
е	2.54			0.1		
Е	10.00		10.28	0.3937		0.4047
E1	8.30		8.70	0.3268		0.3425
E2	6.85		7.25	0.2697		0.2854
G	4.88		5.28	0.1921		0.2079
Н	15		15.85	0.5906		0.6240
L	1.78		2.28	0.0701		0.0898
L2	1.27		1.40	0.0500		0.0551
L3	1.40		1.75	0.0551		0.0689
R		0.40			0.0157	
V2	0°		8°	0°		8°

Notes:

 $^{^{(1)}\}mbox{Dimensions}$ in inches are given for reference only

16.90 10.30 5.08 ----‡1.30 [↓] 3.70 8.90

Figure 13: D²PAK recommended footprint (dimensions are in mm)

TN1605H-6G Ordering information

3 Ordering information

Figure 14: Ordering information scheme

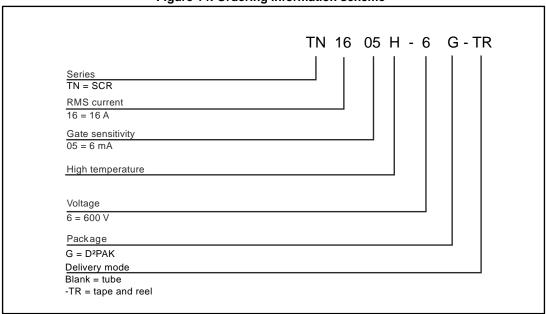


Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN1605H-6G	TN1605H6	D2D A IZ	15 ~	50	Tube
TN1605H-6G-TR	TINTOUSING	D²PAK	1.5 g	1000	Tape and reel

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
18-May-2017	1	Initial release.
26-Jun-2017	2	Updated Table 5: "Thermal resistance".

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